

L Number	Hits	Search Text	DB	Time stamp
27	477	@ad<=19980907 and 'doped polysilicon gates'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:58
29	6	@ad<=19980907 and 'polysilicon gates' with 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:05
32	6	@ad<=19980907 and 'polysilicon gates' with 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:06
33	3	@ad<=19980907 and 'polysilicon gates' with ferroelectric with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:11
34	1041	@ad<=19980907 and ferroelectric with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:12
35	6	@ad<=19980907 and ferroelectric with 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:12
-	92	@ad<=19980907 and 'ferroelectric transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:00
-	1	"4047214".PN.	USPAT	2002/09/09 09:51
-	1	"4161038".PN.	USPAT	2002/09/09 09:51
-	1	"5424238".PN.	USPAT	2002/09/09 09:51
-	1	"5654568".PN.	USPAT	2002/09/09 09:52
-	1	"3808674".PN.	USPAT	2002/09/09 10:02
-	1	"5146299".PN.	USPAT	2002/09/09 10:02
-	1	"5361225".PN.	USPAT	2002/09/09 10:02
-	1	"5424238".PN.	USPAT	2002/09/09 10:22
-	3397	((438/3) or (257/295-296)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
-	2344	((438/3) or (257/295-296)).CCLS.) and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 10:46
-	1	"4460670".PN.	USPAT	2002/09/09 10:36
-	658	((((438/3) or (257/295-296)).CCLS.) and @ad<=19980907) and 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 10:46
-	1	"5530668".PN.	USPAT	2002/09/09 11:09
-	1	"5530667".PN.	USPAT	2002/09/09 11:09
-	1	"5317533".PN.	USPAT	2002/09/09 11:10
-	1	"5289408".PN.	USPAT	2002/09/09 11:10
-	0	@ad<=19980907 and 'ferroelectric transistor' with surrounding adj gate	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 11:58

	0	@ad<=19980907 and 'ferroelectric' with surrounding adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 11:58
	31	@ad<=19980907 and 'ferroelectric' and 'surrounding gate transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 16:35
	1191	((257/324) or (257/410-411)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 14:57
	954	((((257/324) or (257/410-411)).CCLS.) and @ad<=19980907	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 14:58
	46	(((257/324) or (257/410-411)).CCLS.) and @ad<=19980907) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 14:58
	45	@ad<=19980907 and 'gate dielectric' with 'ferroelectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/09 15:47
	311	@ad<=19980907 and ferroelectric near transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 08:52
	2	@ad<=19980907 and 'gate insulator' with 'ferroelectric' and 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 08:57
	7813	@ad<=19980907 and 'polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:56
	79	(@ad<=19980907 and 'polysilicon gate') and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 12:04
	13	@ad<=19980907 and 'ferroelectric transistor' and 'diode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:46
	1149	@ad<=19980907 and 'stacked gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:02
	14	(@ad<=19980907 and 'stacked gate') and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/10 11:02